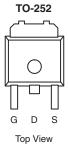


# P-Channel 60-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)	
- 60	0.060 at V <sub>GS</sub> = - 10 V	- 19	26	
- 60	0.077 at V <sub>GS</sub> = - 4.5 V	- 16.8	20	





**FEATURES** 

- TrenchFET<sup>®</sup> Power MOSFET
- 175 °C Junction Temperature



Drain Connected to Tab

Ordering Information: SUD19P06-60L-E3 (Lead (Pb)-free)

s O GO

P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25 \degree C$ , unless otherwise noted					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V <sub>DS</sub>	- 60	v		
Gate-Source Voltage		V <sub>GS</sub>			± 20
Continuous Drain Current (T $= 175$ °C)	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	- 19	А	
Continuous Drain Current (T <sub>J</sub> = 175 °C)	T <sub>C</sub> = 125 °C		- 11		
Pulsed Drain Current		I <sub>DM</sub>	- 30	A	
Avalanche Current, Single Pulse		I <sub>AS</sub>	- 22		
Repetitive Avalanche Energy, Single Pulse <sup>a</sup>		E <sub>AS</sub>	24.2	mJ	
Power Dissipation	$T_{\rm C} = 25 ^{\circ}{\rm C}$ $P_{\rm D}$	46 <sup>c</sup>	w		
	T <sub>A</sub> = 25 °C		2.7 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
hundling to Angling b	t ≤ 10 s	R <sub>thJA</sub>	17	21	°C/W
Junction-to-Ambient <sup>D</sup>	Steady State		45	55	
Junction-to-Case		R <sub>thJC</sub>	2.7	3.25	

Notes:

a. Duty cycle  $\leq$  1 %.

b. When monuted on 1" square PCB (FR-4 material).

c. See SOA curve for voltage derating.

# SUD19P06-60L

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Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static	·	· · · ·					
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 V, I_D = -250 \mu A$	- 60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \ \mu A$	- 1		- 3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = -60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1		
	I <sub>DSS</sub>	$V_{DS}$ = - 60 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 °C			- 50	μA	
		$V_{DS}$ = - 60 V, $V_{GS}$ = 0 V, $T_{J}$ = 175 ° C			- 150	1	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 V, V_{GS} = -10 V$	- 30			А	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A		0.048	0.060	Ω	
Drain Course On State Desistance	r	$V_{GS}$ = - 10 V, I <sub>D</sub> = - 16.8 A, T <sub>J</sub> = 125 °C			0.102		
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS}$ = - 10 V, $I_{D}$ = - 16.8 A, $T_{J}$ = 175 °C			0.129		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A		0.061	0.077		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 10 A		22		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			1140	1710	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$ , $V_{DS} = -25 V$ , f = 1 MHz		130			
Reverse Transfer Capacitance	C <sub>rss</sub>			90			
Total Gate Charge	Qg			26	40	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = - 30 V, $V_{GS}$ = - 10 V, $I_{D}$ = - 10 A		4.5			
Gate-Drain Charge	Q <sub>gd</sub>			7.0			
Gate Resistance	R <sub>g</sub>	f = 1 MHz		7.0		Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 30 V, $R_L$ = 3 $\Omega$		9	15		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong$ - 19 A, $\text{V}_\text{GEN}$ = - 10 V, $\text{R}_\text{g}$ = 2.5 $\Omega$		65	100	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			30	45	1	
Drain-Source Body Diode Characterist	<b>cs</b> (T <sub>C</sub> = 25 °C)	þ		•			
Continuous Current	۱ <sub>S</sub>				- 30	A	
Pulsed Current	I <sub>SM</sub>				- 30		
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 19 A, V <sub>GS</sub> = 0 V		- 1.0	- 1.5	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 19 A, di/dt = 100 A/μs		41	61	ns	

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

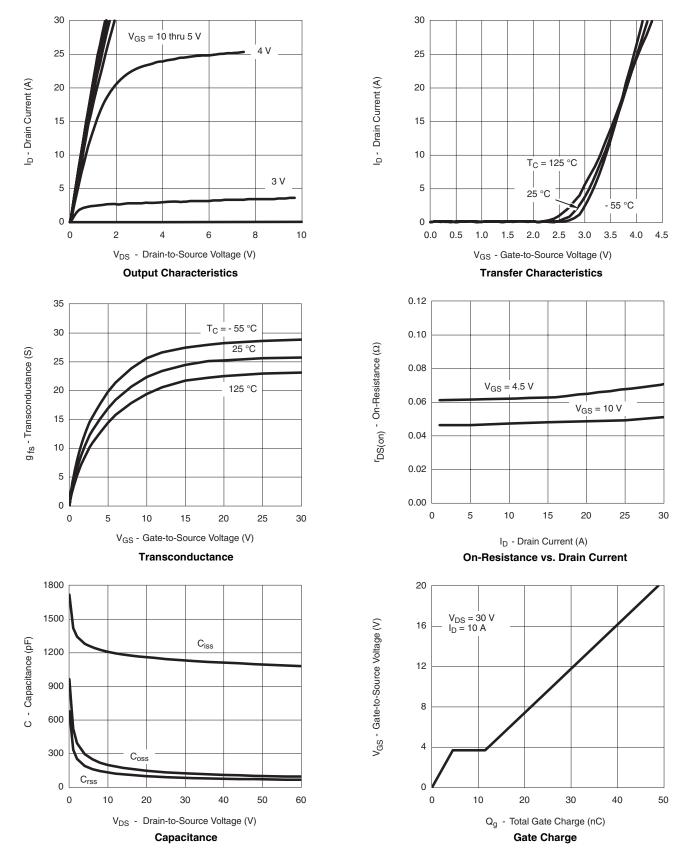
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



## SUD19P06-60L

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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

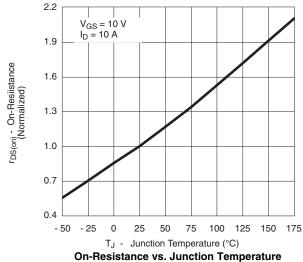


Document Number: 73103 S-71660-Rev. B, 06-Aug-07

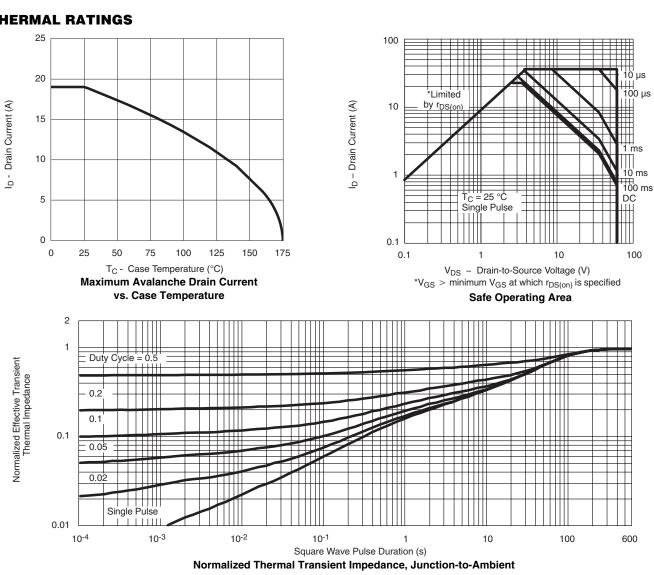
## SUD19P06-60L

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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







IS - Source Current (A) 10 T<sub>J</sub> = 150 °C T<sub>J</sub> = 25 °C 1 0.0 0.3 0.6 0.9 1.2 V<sub>SD</sub> - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage

40

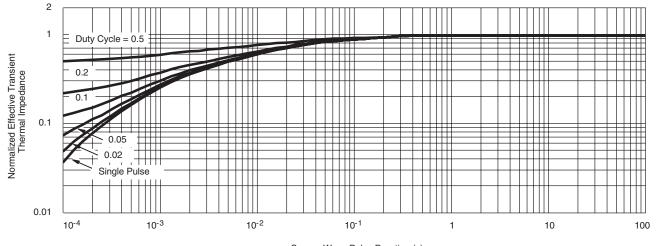
4



1.5



### THERMAL RATINGS



Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?73103

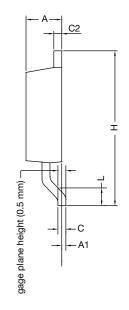


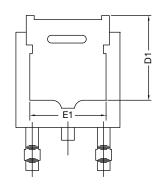


**TO-252AA Case Outline** 

### VERSION 1: FACILITY CODE = Y







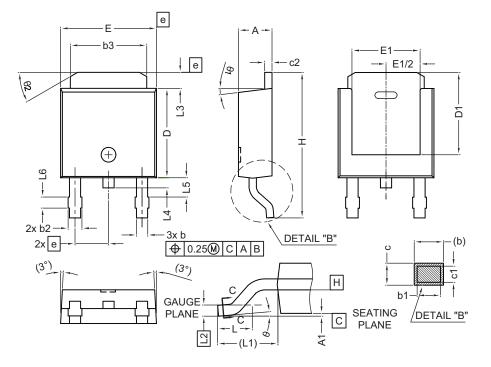
	MILLIMETERS			
DIM.	MIN.	MAX.		
А	2.18	2.38		
A1	-	0.127		
b	0.64	0.88		
b2	0.76	1.14		
b3	4.95	5.46		
С	0.46	0.61		
C2	0.46	0.89		
D	5.97	6.22		
D1	4.10	-		
E	6.35	6.73		
E1	4.32	-		
Н	9.40	10.41		
е	2.28 BSC			
e1	4.56	4.56 BSC		
L	1.40	1.78		
L3	0.89	1.27		
L4	-	1.02		
L5	1.01	1.52		

#### Note

• Dimension L3 is for reference only



### VERSION 2: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
A	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	-	
E	6.35	6.73	
E1	4.32	-	
e	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	l ref.	
L2	0.51	BSC	
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

#### Notes

• Dimensioning and tolerance confirm to ASME Y14.5M-1994

• All dimensions are in millimeters. Angles are in degrees

• Heat sink side flash is max. 0.8 mm

Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022 DWG: 5347

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### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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